

Important notice

Dear Customer,

On 7 February 2017 the former NXP Standard Product business became a new company with the tradename **Nexperia**. Nexperia is an industry leading supplier of Discrete, Logic and PowerMOS semiconductors with its focus on the automotive, industrial, computing, consumer and wearable application markets

In data sheets and application notes which still contain NXP or Philips Semiconductors references, use the references to Nexperia, as shown below.

Instead of http://www.nxp.com, http://www.nxp.com, http://www.nexperia.com/, http://www.nexperia.com/, use http://www.nexperia.com/

Instead of sales.addresses@www.nxp.com or sales.addresses@www.semiconductors.philips.com, use salesaddresses@nexperia.com (email)

Replace the copyright notice at the bottom of each page or elsewhere in the document, depending on the version, as shown below:

- © NXP N.V. (year). All rights reserved or © Koninklijke Philips Electronics N.V. (year). All rights reserved

Should be replaced with:

- © Nexperia B.V. (year). All rights reserved.

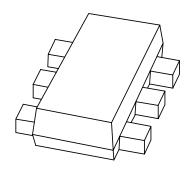
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PEMZ7 NPN/PNP general purpose transistors

Product data sheet Supersedes data of 2001 Sep 25 2001 Nov 07



NPN/PNP general purpose transistors

PEMZ7

FEATURES

- 300 mW total power dissipation
- Very small 1.6 × 1.2 mm ultra thin package
- · Self alignment during soldering due to straight leads
- · Low collector capacitance
- Low V_{CEsat}
- High current capabilities
- Improved thermal behaviour due to flat leads
- · Reduced required PCB area
- · Reduced pick and place costs.

APPLICATIONS

- Heavy duty battery powered equipment (automotive, telecom and audio-video) such as motor and lamp drivers
- V_{CEsat} critical applications such as latest low supply voltage IC applications
- All battery driven equipment, to save battery power.

DESCRIPTION

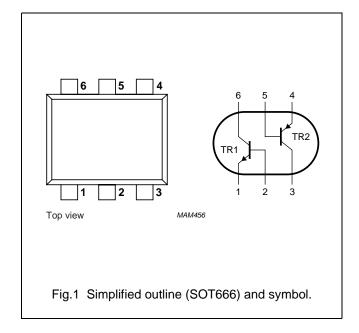
NPN/PNP low V_{CEsat} transistor pair in a SOT666 plastic package.

MARKING

TYPE NUMBER	MARKING CODE		
PEMZ7	Z7		

PINNING

PIN	DESCRIPTION		
1, 4	emitter	TR1; TR2	
2, 5	base	TR1; TR2	
6, 3	collector	TR1; TR2	



NPN/PNP general purpose transistors

PEMZ7

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT		
Per transis	Per transistor; for the PNP transistor with negative polarity						
V _{CBO}	collector-base voltage	open emitter	_	15	V		
V_{CEO}	collector-emitter voltage	open base	_	12	V		
V_{EBO}	emitter-base voltage	open collector	_	6	V		
Ic	collector current (DC)		_	500	mA		
I _{CM} peak collector current			_	1	Α		
I _{BM}	peak base current		_	100	mA		
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	200	mW		
T _{stg}	storage temperature		-65	+150	°C		
Tj	junction temperature		_	150	°C		
T _{amb} operating ambient temperature			-65	+150	°C		
Per device	Per device						
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	_	300	mW		

Note

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to ambient	notes 1 and 2	416	K/W

Notes

- 1. Transistor mounted on an FR4 printed-circuit board.
- 2. The only recommended soldering method is reflow soldering.

^{1.} Transistor mounted on an FR4 printed-circuit board.

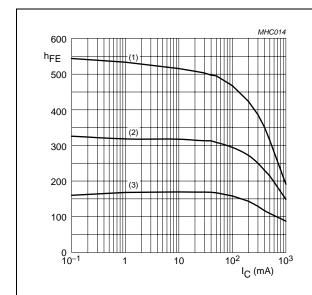
NPN/PNP general purpose transistors

PEMZ7

CHARACTERISTICS

 T_{amb} = 25 °C; unless otherwise specified.

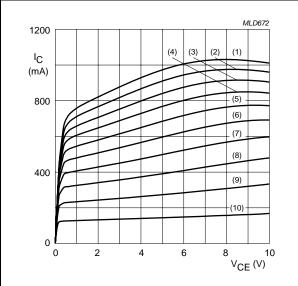
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Per transis	Per transistor; for the PNP transistor with negative polarity						
I _{CBO}	collector-base cut-off current	V _{CB} = 15 V; I _E = 0	_	_	100	nA	
		V _{CB} = 15 V; I _E = 0; T _j = 150 °C	_	_	50	μΑ	
I _{EBO}	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0	_	_	100	nA	
h _{FE}	DC current gain	V _{CE} = 2 V; I _C = 10 mA	200	_	_		
V _{CEsat}	collector-emitter saturation voltage	I _C = 200 mA; I _B = 10 mA	_	_	220	mV	
f_{T}	transition frequency	I _C = 100 mA; V _{CE} = 5 V;					
	TR1 (NPN)	f = 100 MHz	250	420	_	MHz	
	TR2 (PNP)		100	280	_	MHz	
C _c	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$					
	TR1 (NPN)		_	4.4	6	pF	
	TR2 (PNP)		_	_	10	pF	



TR1 (NPN); V_{CE} = 2 V.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.2 DC current gain as a function of collector current; typical values.



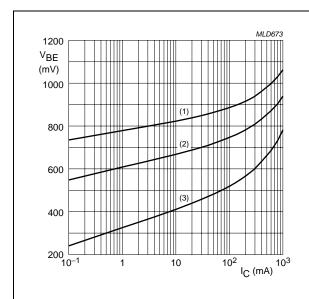
TR1 (NPN); T_{amb} = 25 °C.

- (1) $I_B = 4.60 \text{ mA}$
- (5) $I_B = 2.76 \text{ mA}$
- (9) $I_B = 0.92 \text{ mA}$ (10) $I_B = 0.46 \text{ mA}$
- (2) $I_B = 4.14 \text{ mA}$ (3) $I_B = 3.68 \text{ mA}$
- (6) $I_B = 2.30 \text{ mA}$ (7) $I_B = 1.84 \text{ mA}$
- (4) $I_B = 3.22 \text{ mA}$ (8) $I_B = 1.38 \text{ mA}$

Fig.3 Collector current as a function of collector-emitter voltage; typical values.

NPN/PNP general purpose transistors

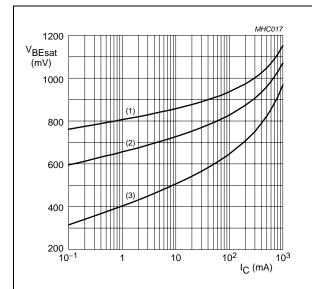
PEMZ7



TR1 (NPN); $V_{CE} = 2 V$.

- (1) $T_{amb} = -55 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

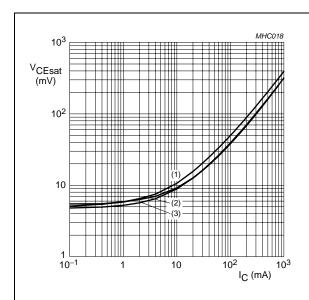
Fig.4 Base-emitter voltage as a function of collector current; typical values.



TR1 (NPN); $I_C/I_B = 20$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

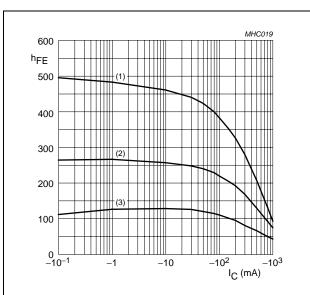
Fig.5 Base-emitter saturation voltage as a function of collector current; typical values.



TR1 (NPN); $I_{\text{C}}/I_{\text{B}} = 20.$

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.6 Collector-emitter saturation voltage as a function of collector current; typical values.



TR2 (PNP); $V_{CE} = -2 \text{ V}.$

- (1) $T_{amb} = 150 \,^{\circ}C$.
- (2) $T_{amb} = 25 \,^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.7 DC current gain as a function of collector current; typical values.

NPN/PNP general purpose transistors

PEMZ7

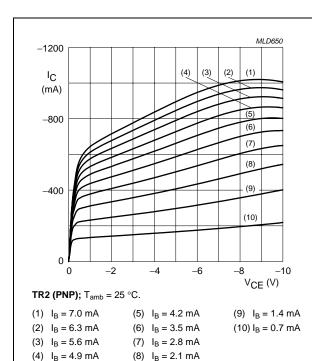
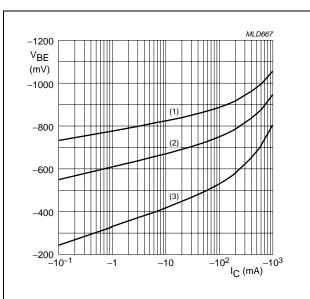


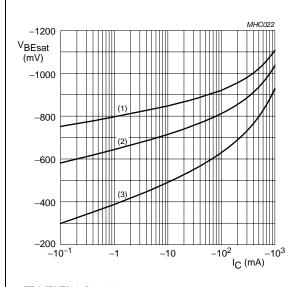
Fig.8 Collector current as a function of collector-emitter voltage; typical values.



TR2 (PNP); $V_{CE} = -2 V$.

- (1) $T_{amb} = -55$ °C.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = 150 \, ^{\circ}C$.

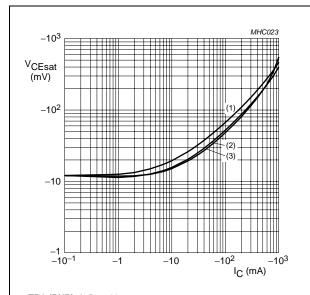
Fig.9 Base-emitter voltage as a function of collector current; typical values.



TR2 (PNP); $I_C/I_B = 20$.

- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) T_{amb} = 25 °C.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.10 Base-emitter saturation voltage as a function of collector current; typical values.



TR2 (PNP); $I_C/I_B = 20$.

- (1) $T_{amb} = 150 \,^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.11 Collector-emitter saturation voltage as a function of collector current; typical values.

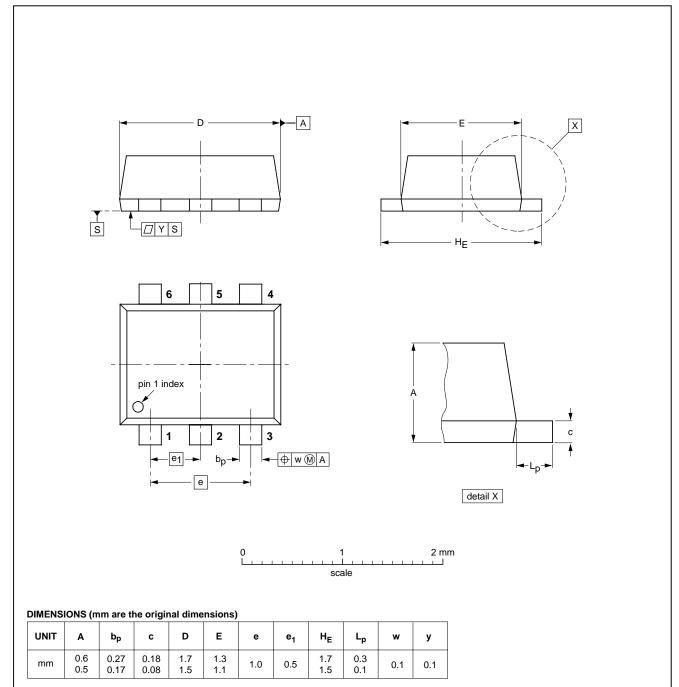
NPN/PNP general purpose transistors

PEMZ7

PACKAGE OUTLINE

Plastic surface mounted package; 6 leads

SOT666



OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATE		ISSUE DATE
VERSION	IEC	JEDEC	EIAJ		PROJECTION	1330E DATE
SOT666						-01-01-04 01-08-27

NPN/PNP general purpose transistors

PEMZ7

DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

DISCLAIMERS

General — Information in this document is believed to be accurate and reliable. However, NXP Semiconductors does not give any representations or warranties, expressed or implied, as to the accuracy or completeness of such information and shall have no liability for the consequences of use of such information.

Right to make changes — NXP Semiconductors reserves the right to make changes to information published in this document, including without limitation specifications and product descriptions, at any time and without notice. This document supersedes and replaces all information supplied prior to the publication hereof.

Suitability for use — NXP Semiconductors products are not designed, authorized or warranted to be suitable for use in medical, military, aircraft, space or life support equipment, nor in applications where failure or malfunction of an NXP Semiconductors product can reasonably be expected to result in personal injury, death or severe property or environmental damage. NXP Semiconductors accepts no liability for inclusion and/or use of NXP Semiconductors products in such equipment or applications and therefore such inclusion and/or use is at the customer's own risk.

Applications — Applications that are described herein for any of these products are for illustrative purposes only. NXP Semiconductors makes no representation or warranty that such applications will be suitable for the specified use without further testing or modification.

Limiting values — Stress above one or more limiting values (as defined in the Absolute Maximum Ratings System of IEC 60134) may cause permanent damage to the device. Limiting values are stress ratings only and operation of the device at these or any other conditions

above those given in the Characteristics sections of this document is not implied. Exposure to limiting values for extended periods may affect device reliability.

Terms and conditions of sale — NXP Semiconductors products are sold subject to the general terms and conditions of commercial sale, as published at http://www.nxp.com/profile/terms, including those pertaining to warranty, intellectual property rights infringement and limitation of liability, unless explicitly otherwise agreed to in writing by NXP Semiconductors. In case of any inconsistency or conflict between information in this document and such terms and conditions, the latter will prevail.

No offer to sell or license — Nothing in this document may be interpreted or construed as an offer to sell products that is open for acceptance or the grant, conveyance or implication of any license under any copyrights, patents or other industrial or intellectual property rights.

Export control — This document as well as the item(s) described herein may be subject to export control regulations. Export might require a prior authorization from national authorities.

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

NXP Semiconductors

Customer notification

This data sheet was changed to reflect the new company name NXP Semiconductors. No changes were made to the content, except for the legal definitions and disclaimers.

Contact information

For additional information please visit: http://www.nxp.com

For sales offices addresses send e-mail to: salesaddresses@nxp.com

© NXP B.V. 2009

All rights are reserved. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner.

The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice. No liability will be accepted by the publisher for any consequence of its use. Publication thereof does not convey nor imply any license under patent- or other industrial or intellectual property rights.

Printed in The Netherlands 613514/02/pp9 Date of release: 2001 Nov 07 Document order number: 9397 750 09054



X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - BJT category:

Click to view products by Nexperia manufacturer:

Other Similar products are found below:

619691C MCH4017-TL-H BC546/116 BC557/116 BSW67A NTE158 NTE187A NTE195A NTE2302 NTE2330 NTE63 C4460
2SA1419T-TD-H 2SA1721-O(TE85L,F) 2SA2126-E 2SB1204S-TL-E 2SD2150T100R SP000011176 FMMTA92QTA 2N2369ADCSM
2N5769 2SC2412KT146S 2SC5490A-TL-H 2SD1816S-TL-E 2SD1816T-TL-E CMXT2207 TR CPH6501-TL-E MCH4021-TL-E
US6T6TR NJL0281DG 732314D CMXT3906 TR CPH3121-TL-E CPH6021-TL-H 873787E IMZ2AT108 UMX21NTR MCH6102-TL-E
NJL0302DG 2N3583 2SA1434-TB-E 2SC3143-4-TB-E 2SD1621S-TD-E NTE103 30A02MH-TL-E NSV40301MZ4T1G NTE101 NTE13
NTE15 NTE16001